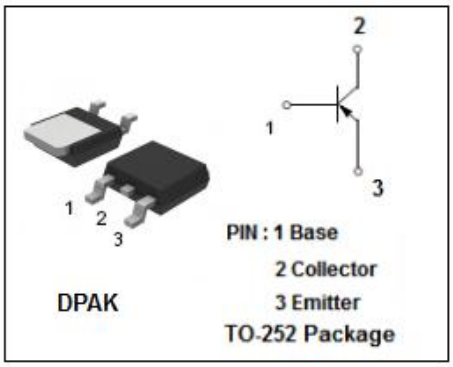
isc Silicon PNP Power Transistor — 2SA1400Z

DESCRIPTION

- High Collector-Emitter Voltage -
  : V_{CEO}= -400V(Min)
- Complement to Type 2SC3588Z
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

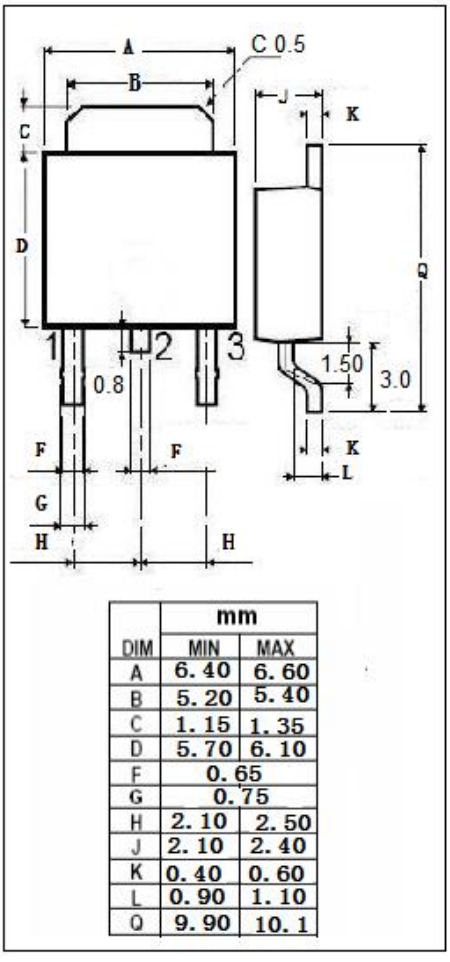


APPLICATIONS

- Designed for high voltage switching ,especially in Hybrid integrated cricuits.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-400	V
V_{CEO}	Collector-Emitter Voltage	-400	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current-Continuous	-0.5	A
P_C	Collector Power Dissipation @ T_C=25℃	2.0	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	6.40	6.60
B	5.20	5.40
C	1.15	1.35
D	5.70	6.10
F	0.65	
G	0.75	
H	2.10	2.50
J	2.10	2.40
K	0.40	0.60
L	0.90	1.10
Q	9.90	10.1

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= -0.1mA; I_B= 0	-400			V
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -1mA; I_B= 0	--400			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= -0.1mA; I_C= 0	-7			V
I_{CBO}	Collector Cutoff Current	V_{CB}= -400V; I_E= 0			-100	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0			-10	μA
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -100mA; I_B= -10mA			-1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -100mA; I_B= -10mA			-1.2	V
h_{FE}	DC Current Gain	I_C= -50mA; V_{CE}= -5V	30		200	

◆ **h_{FE} Classifications**

N	M	L	K
30-60	40-80	60-120	100-200